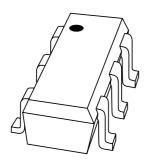
DISCRETE SEMICONDUCTORS

DATA SHEET



BAS16VYHigh-speed switching diode array

Product specification

2003 Apr 08





High-speed switching diode array

BAS16VY

FEATURES

- Small plastic SMD package
- · High switching speed
- Three electrically isolated diodes
- · Low capacitance.

APPLICATIONS

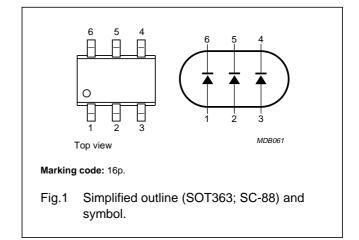
• General purpose switching in surface mounted circuits.

DESCRIPTION

The BAS16VY consists of three electrically isolated high-speed switching diodes, encapsulated in a small SOT363 (SC-88) SMD plastic package.

PINNING

PIN	DESCRIPTION	
1	anode (a1)	
2	anode (a2)	
3	anode (a3)	
4	cathode (k3)	
5	cathode (k2)	
6	cathode (k1)	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per diode	Per diode						
V _{RRM}	repetitive peak reverse voltage		_	85	V		
V _R	continuous reverse voltage		_	75	V		
I _F	continuous forward current		_	200	mA		
I _{FRM}	repetitive peak forward current		_	450	mA		
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4					
		t = 1 μs	_	4.5	Α		
		t = 1 ms	_	1	Α		
		t = 1 s	_	0.5	Α		
P _{tot}	total power dissipation	T _s = 85 °C; note 1	_	250	mW		
T _{stg}	storage temperature		-65	+150	°C		
T _j	junction temperature		-65	+150	°C		

Note

1. Solder points at pins: 2, 3, 5 and 6.

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT		
Per diode						
V _F	forward voltage	see Fig.3				
		I _F = 1 mA	715	mV		
		I _F = 10 mA	855	mV		
		I _F = 50 mA	1	V		
		I _F = 150 mA	1.25	V		
I _R	reverse current	see Fig.5				
		V _R = 25 V	30	nA		
		V _R = 75 V	1	μΑ		
		V _R = 25 V; T _j = 150 °C	30	μΑ		
		V _R = 75 V; T _j = 150 °C	50	μΑ		
C _d	diode capacitance	capacitance $f = 1 \text{ MHz}$; $V_R = 0$; see Fig.6		pF		
t _{rr}	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 10$ mA; $I_R = 10$ mA; $I_R = 10$ mA; $I_R = 1$ mA; see Fig.7		ns		
V _{fr}	orward recovery voltage when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8		1.75	V		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	note 1	≤260	K/W

Note

1. Solder points at pins: 2, 3, 5 and 6.

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GRAPHICAL DATA

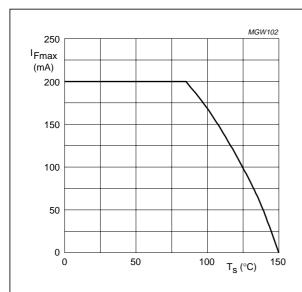
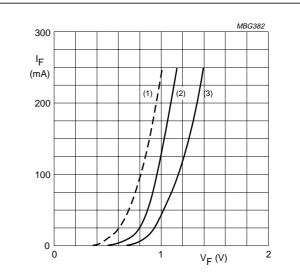
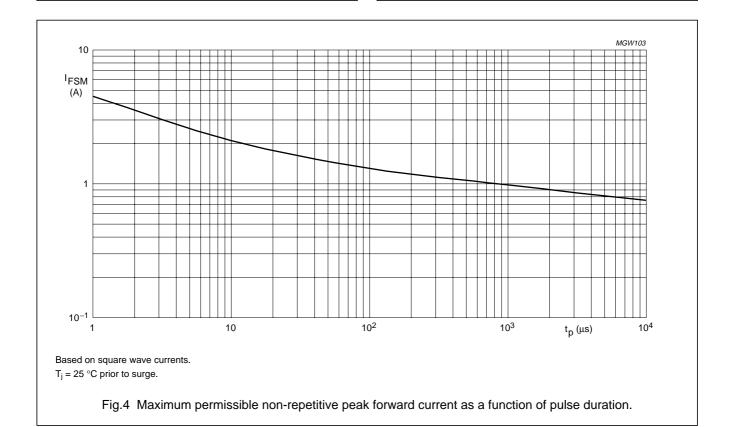


Fig.2 Maximum permissible continuous forward current as a function of soldering point temperature.



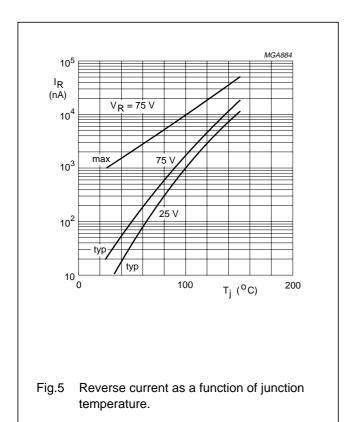
- (1) $T_j = 150$ °C; typical values.
- (2) $T_i = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



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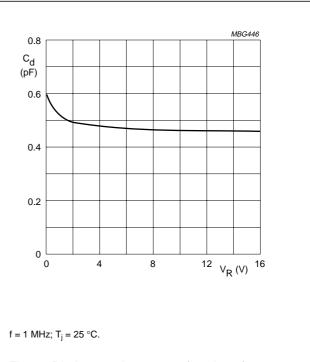


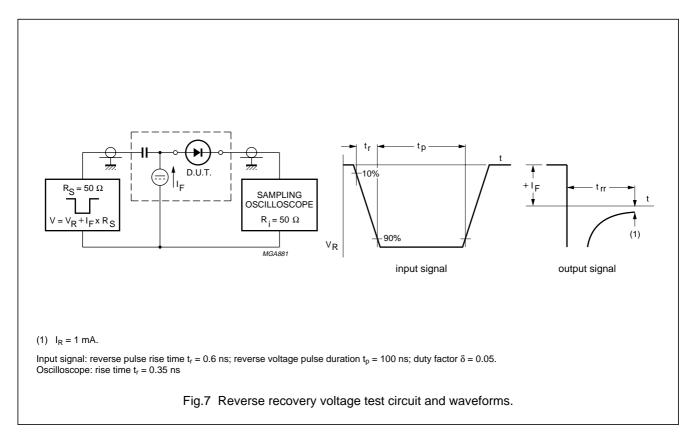
Fig.6 Diode capacitance as a function of reverse voltage; typical values.

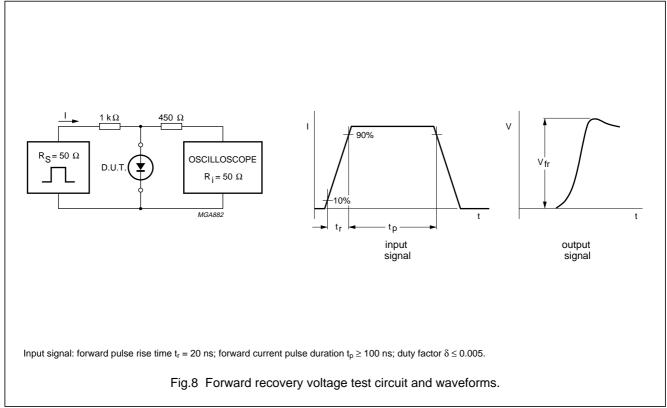
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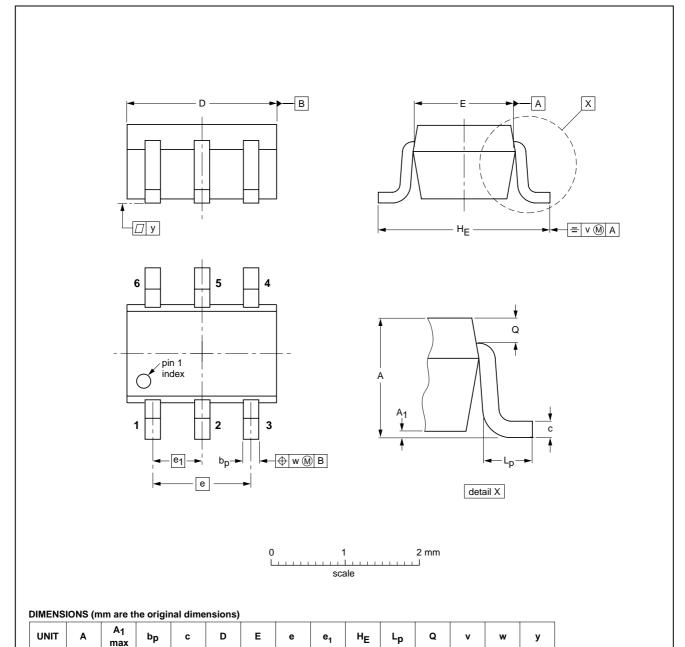
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT363			SC-88		97-02-28

0.65

0.45 0.15 0.25 0.15

0.2

0.1

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0.25 0.10

0.30

0.20

1.1 0.8

mm

0.1

2.2 1.8 1.35 1.15

1.3

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LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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NOTES

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NOTES

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Printed in The Netherlands

613514/01/pp12

Date of release: 2003 Apr 08

Document order number: 9397 750 10909

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